

Ultra-Fast Recovery Diodes 8A FRED

Features

- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- : Tin plated leads, solderable per J-STD- and JESD22-B102



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Device marking code			MUR8120F
Repetitive Peak Reverse Voltage	V_{RRM}	V	1200
Average Rectified Output Current @60Hz sine wave, R-load, Tc(FIG.1)	I_O	A	8
Surge(Non-repetitive) Forward Current @60Hz half sine-wave, 1 cycle, Tj=25	I_{FSM}	A	60
Current Squared Time @1ms t 8.3ms Tj=25	I^2t	A ² s	14.94
Storage Temperature	T_{stg}		-55 ~ +150
Junction Temperature	T_j		-55 ~ +150
Junction capacitance @4V,1MHz	C_j	pF	26
Mounting torque@recommend torque 5kg cm	Tor	kg cm	8



Electrical Characteristics

PARAMETER	SYMBOL	UNIT				
Instantaneous forward voltage drop per diode	V_{FM}	V	$I_{FM}=8.0A @T_j=125$			
					1.70	2.10
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	$V_{RM}=V_{RRM}$ $T_j=25$	-	-	5.0
	I_{RRM2}			$V_{RM}=V_{RRM}$		



Outline Dimensions

ITO-220AC		
Dim	Min	Max
A	9.8	10.2
B	2.25	2.75
C	2.95	3.45
D	14.75	15.25
E	3.5	4.1
F	0.45	0.75
G	0.45	0.75
H	13.35	14.15
I	4.97	5.23
J	4.3	4.8
K	4.	



MUR8120F

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